

WHAT IS CLAIMED IS:

1. A semiconductor integrated circuit device on one semiconductor substrate, comprising:
 - a memory array;
 - a sense amplifier coupled to receive an output of the memory array, wherein the sense amplifier has an input for a sense amplifier activation signal;
 - a timing controller having an output coupled to the input of sense amplifier, wherein said timing controller includes:
 - a plurality of delay circuits coupled serially,
 - a decoder to select one or more of the plurality of delay circuits;
 - a volatile storage circuit which stores information and which is coupled to the decoder; and
 - electrically programmable nonvolatile memory elements having high or low threshold voltages that determine the information stored therein.
2. A semiconductor integrated circuit device according to claim 1, wherein the information stored in the electrically programmable nonvolatile memory elements is read out in response to an initialization of the semiconductor integrated circuit device.
3. A semiconductor integrated circuit device according to claim 1, wherein each of the electrically programmable nonvolatile memory elements includes a location where electrons are to be charged.

4. A semiconductor integrated circuit device according to claim 3, wherein said location where electrons are to be stored is a floating gate.

5. A semiconductor integrated circuit device according to claim 1, wherein each of the electrically programmable nonvolatile memory elements includes a control gate and a floating gate.

6. A semiconductor integrated circuit device according to claim 1, wherein the memory array includes a plurality of static type memory cells.